KRA2206S

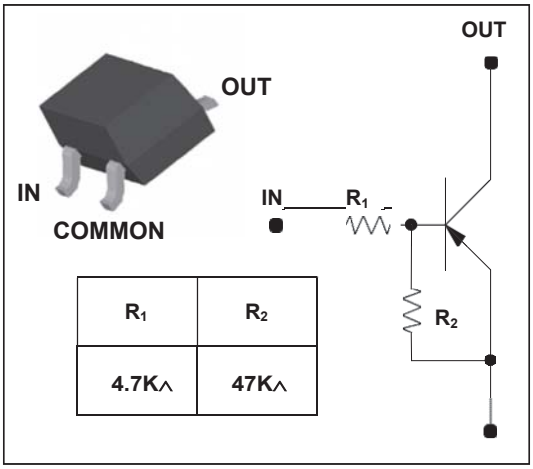
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- High packing density
- PNP Silicon Transistor

MECHANICAL DATA

- Case style:SOT-23 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Characteristic	Symbol	Rating	Unit
Output voltage	V_O	-50	V
Input voltage	V_I	-20, 5	V
Output current	I_O	-100	mA
Power dissipation	P_D	200	mW
Junction temperature	T_J	150	°C
Storage temperature range	T_{stg}	-55 ~ 150	°C

Electrical Characteristics (Ratings at 25℃ ambient temperature unless otherwise specified).

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Output cut-off current	$I_{O(OFF)}$	V_O=-50V, V_I=0	-	-	-500	nA
DC current gain	G_I	V_O=-5V, I_O=-10mA	80	200	-	-
Output voltage	$V_{O(ON)}$	I_O=-10mA, I_I=-0.5mA	-	-0.1	-0.3	V
Input voltage (ON)	$V_{I(ON)}$	V_O=-0.2V, I_O=-5mA	-	-0.9	-1.3	V
Input voltage (OFF)	$V_{I(OFF)}$	V_O=-5V, I_O=-0.1mA	-0.5	-0.65	-	V
Transition frequency	f_T*	V_O=-10V, I_O=-5mA, f=1MHz	-	200	-	MHz
Input current	I_I	V_I=-5V, I_O=0	-	-	-1.8	mA
Input resistor (Input to base)	R_1	-	3.3	4.7	6.1	KΩ
Input resistor (Base to common)	R_2	-	33	47	61	KΩ

* : Characteristic of transistor only

RATINGSAND CHARACTERISTIC CURVES

Fig. 1 Pc - Ta

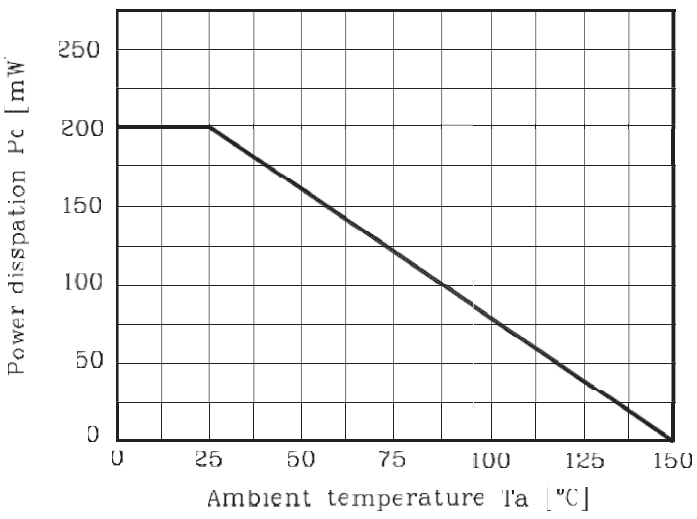


Fig. 2 I_O - $V_{I(ON)}$

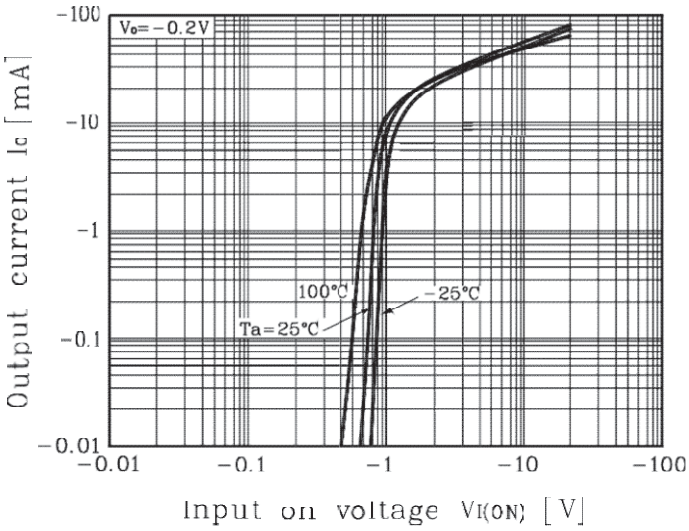


Fig. 3 I_O - $V_{I(OFF)}$

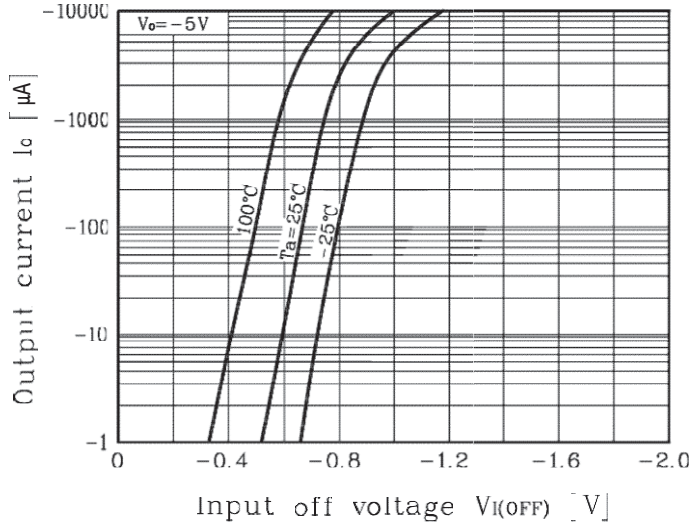
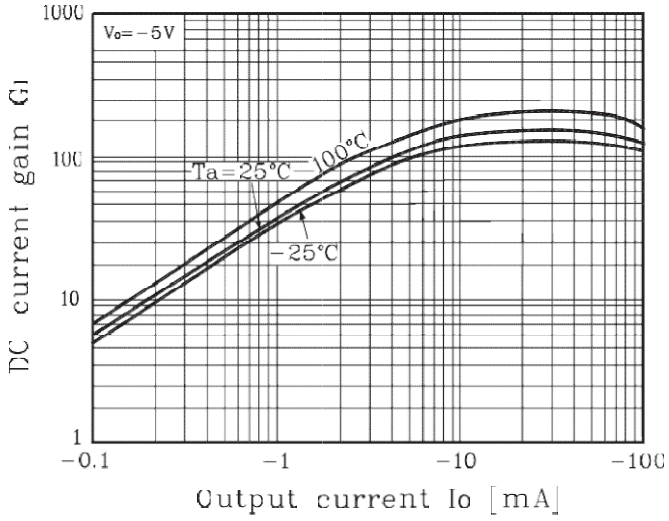
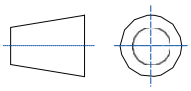
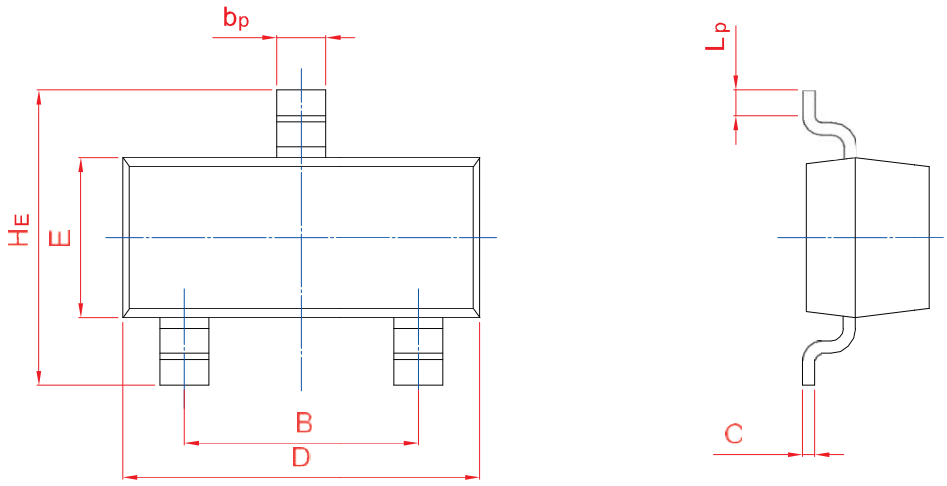


Fig. 4 G_I - I_O







UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20